# IS25C128A



# 128K-bit SPI SERIAL ELECTRICALLY ERASABLE PROM

Advanced Information JUNE 2007

### **FEATURES**

- Serial Peripheral Interface (SPI) Compatible
  - Supports SPI Modes 0 (0,0) and 3 (1,1)
- LowpowerCMOS
  - Active current less than 3.0 mA (1.8V)
  - Standby current less than 15 µA (1.8V)
- Low-voltage Operation
  - Vcc = 1.8V to 5.5V
- · Block Write Protection
  - Protect 1/4, 1/2, or Entire Array
- 64 byte page write mode
  - Partial page writes allowed
- 10 MHz Clock Rate (5V)
- Self timed write cycles
  - 5ms max @ 2.5V
- · High-reliability
  - Endurance: 1,000,000 cycles
  - Data retention: 40 years
- 8-pin SOIC, 8-pin TSSOP and 8-pin PDIP packages available
- Industrial and Automotive temperature ranges

#### DESCRIPTION

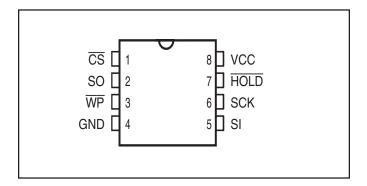
The IS25C128A is electrically erasable PROM devices that use the Serial Peripheral Interface (SPI) for communications. The IS25C128A is 128Kbit (16K x 8). The IS25C128A EEPROMs is offered in a wide operating voltage range of 1.8V to 5.5V for compatibility with most application voltages. ISSI designed the IS25C128A to be an efficient SPI EEPROM solution. The devices are packaged in 8-pin JEDEC SOIC, 8-pin EIAJ SOIC, 8-pin TSSOP and 8-pin PDIP.

The functional features of the IS25C128A allow them to be among the most advanced serial non-volatile memories available. Each device has a Chip-Select ( $\overline{\textbf{CS}}$ ) pin, and a 3-wire interface of Serial Data In (SI), Serial Data Out (SO), and Serial Clock (SCK). While the 3-wire interface of the IS25C128A provides for high-speed access, a  $\overline{\textbf{HOLD}}$  pin allows the memories to ignore the interface in a suspended state; later the  $\overline{\textbf{HOLD}}$  pin reactivates communication without re-initializing the serial sequence. A Status Register facilitates a flexible write protection mechanism, and a device-ready bit ( $\overline{\textbf{RDY}}$ ).

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# PIN CONFIGURATION 8-Pin DIP, TSSOP and SOIC



#### PIN DESCRIPTIONS

CS	Chip Select
SCK	Serial Data Clock
SI	Serial Data Input
SO	Serial Data Output
GND	Ground
Vcc	Power
WP	Write Protect
HOLD	Suspends Serial Input

### PIN DESCRIPTIONS

**Serial Clock (SCK):** This timing signal provides synchronization between the microcontroller and IS25C128A. Op-Codes, byte addresses, and data are latched on SI with a rising edge of the SCK. Data on SO is refreshed on the falling edge of SCK for SPI modes (0,0) and (1,1).

**Serial Data Input (SI):** This is the input pin for all data that the IS25C128A is required to receive.

**Serial Data Output (SO):** This is the output pin for all data transmitted from the IS25C128A.

Chip Select (CS): The CS pin activates the device. Upon power-up, CS should follow Vcc. When the device is to be enabled for instruction input, the signal requires a High-to-Low transition. While CS is stable Low, the master and slave will communicate via SCK, SI, and SO signals. Upon completion of communication, CS must be driven High. At this moment, the slave device may start its internal write cycle. When CS is high, the device enters a power-saving standby mode, unless an internal write operation is underway. During this mode, the SO pin becomes high impedance.

Write Protect (WP): The purpose of this input signal is to initiate Hardware Write Protection mode. This mode prevents the Block Protection bits and the WPEN bit in the Status Register from being altered. To cause Hardware Write Protection, WP must be Low at the same time WPEN is 1. WP may be hardwired to Vcc or GND.

HOLD (HOLD): This input signal is used to suspend the device in the middle of a serial sequence and temporarily ignore further communication on the bus (SI, SO, SCK). Together with Chip Select, the HOLD signal allows multiple slaves to share the bus. The HOLD signal transitions must occur only when SCK is Low, and be held stable during SCK transitions. (See Figure 8 for Hold timing) To disable this feature, HOLD may be hardwired to Vcc.



### SERIAL INTERFACE DESCRIPTION

**MASTER:** The device that provides a clock signal.

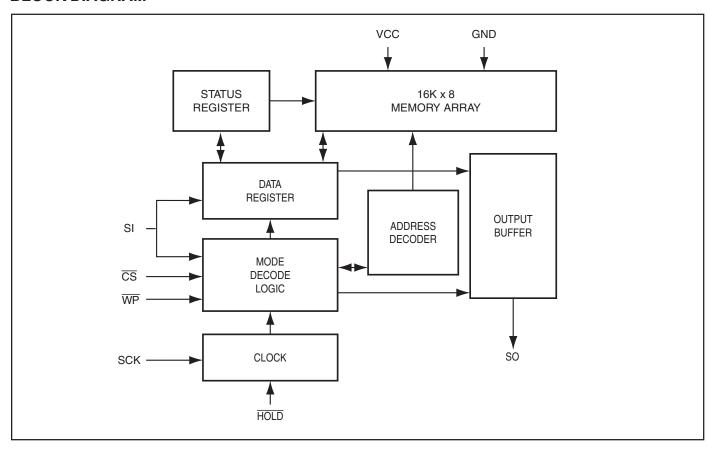
**SLAVE:** The IS25C128A is a slave because the clock signal is an input.

**TRANSMITTER/RECEIVER:** The IS25C128A has both data input (SI) and data output (SO).

**MSB:** The most significant bit. It is always the first bit transmitted or received.

**OP-CODE:** The first byte transmitted to the slave following  $\overline{CS}$  transition to LOW. If the OP-CODE is a valid member of the IS25C128A instruction set (Table 3), then it is decoded appropriately. If the OP-CODE is not valid, and the SO pin remains in high impedance.

# **BLOCK DIAGRAM**





### STATUS REGISTER

The status register contains 8-bits for write protection control and write status. (See Table 1). It is the only region of memory other than the main array that is accessible by the user.

Table 1. Status Register Format

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit1 Bit 0	
WPEN	Χ	Χ	Χ	BP1	BP0	WEN RDY	

#### Notes:

- 1. X = Don't care bit.
- 2. During internal write cycles, bits 0 to 7 are temporarily 1's.

The Status Register is Read-Only if either: a) Hardware Write Protection is enabled or b) WEN is set to 0. If neither is true, it can be modified by a valid instruction.

**Ready (\overline{RDY}), Bit 0:** When  $\overline{RDY} = 1$ , it indicates that the device is busy with a write cycle.  $\overline{RDY} = 0$  indicates that the device is ready for an instruction. If  $\overline{RDY} = 1$ , the only command that will be handled by the device is Read Status Register.

Write Enable (WEN), Bit 1: This bit represents the status of device write protection. If WEN = 0, the Status Register and the entire array is protected from modification, regardless of the setting of WPEN,  $\overline{WP}$  pin, or block protection. The only way to set WEN to 1 is via the Write Enable command (WREN). WEN is reset to 0 upon power-up.

**Block Protect (BP1, BP0), Bits 2-3:** Together, these bits represent one of four block protection configurations implemented for the memory array. (See Table 2 for details.)

BP0 and BP1 are non-volatile cells similar to regular array cells, and factory programmed to 0. The block of memory defined by these bits is always protected, regardless of the setting of WPEN, WP, or WEN.

Table 2. Block Protection

	Sta Regi Bi	ister	Array Addresses Protected
Level	BP1	BP0	IS25C128A
0	0	0	None
1(1/4)	0	1	3000h -3FFFh
2(1/2)	1	0	2000h -3FFFh
3(All)	1	1	0000h -3FFFh

**Don't Care, Bits 4-6:** Each of these bits can receive either 0 or 1, but values will not be retained. When these bits are read from the register, they are always 0.

Write Protect Enable (WPEN), Bit 7: This bit can be used in conjunction with  $\overline{WP}$  pin to enable Hardware Write Protection, which causes the Status Register to be read-only. The memory array is not protected by this mode. Hardware Write Protection requires that  $\overline{WP} = 0$  and WPEN = 1; it is disabled otherwise. Note: WPEN cannot be changed from 1 to 0 if the  $\overline{WP}$  pin is already set to Low. (See Table 4 for data protection relationship)



### **DEVICE OPERATION**

The operations of the IS25C128A are controlled by a set of instructions that are clocked-in serially SI pin. (See Table 3). To begin an instruction, the chip select ( $\overline{CS}$ ) should be dropped Low. Subsequently, each Low-to-High transition of the clock (SK) will latch a stable value on the SI pin. After the 8-bit op-code, it may be appropriate to continue to input an address or data to SI, or to output data from SO. During data output, values appear on the falling edge of SK. All bits are transferred with MSB first. Upon the last bit of communication, but prior to any following Low-to-High transition of SK,  $\overline{CS}$  should be raised High to end the transaction. The device then would enter Standby Mode if no internal programming were underway.

Table 3. Instruction Set

Name	Op-code	Operation	Address	Data(SI)	Data (SO)
WREN	0000 X110	Set Write Enable Latch	-	-	-
WRDI	0000 X100	Reset Write Enable Latch	-	-	-
RDSR	0000 X101	Read Status Register	-	-	D7-D0,
WRSR	0000 X001	Write Status Register	-	D7-D0	-
READ	0000 X011	Read Data from Array	A15-A0	-	D7-D0,
WRITE	0000 X010	Write Data to Array	A15-A0	D7-D0,	-

#### Notes:

- 1. X = Don't care bit. For consistency, it is best to use "0".
- 2. Some address bits are don't care. See Table 5.
- 3. If the bits clocked-in for an op-code are invalid, SO remains high impedance, and upon  $\overline{\textbf{CS}}$  going High there is no affect. A valid op-code with an invalid number of bits clocked-in for address or data will cause an attempt to modify the array or Status Register to be ignored.

#### WRITE ENABLE (WREN)

When Vcc is initially applied, the device powers up with both status register and entire array in a write-disabled state. Upon completion of Write Disable (WRDI), Write Status Register (WRSR), or Write Data to Array (WRITE), the device resets the WEN bit in the Status Register to 0. Prior to any data modification, a WREN instruction is necessary to set WEN to 1. (See Figure 2 for timing).

#### WRITE DISABLE (WRDI)

The device can be completely protected from modification by resetting WEN to 0 through the WRDI instruction. (See Figure 3 for timing).

#### READ STATUS REGISTER (RDSR)

The Read Status instruction tells the user the status of Write Protect Enable, the Block Protection setting (see Table 2), the Write Enable state, and the  $\overline{RDY}$  status. RDSR is the only instruction accepted when a write cycle is underway. It is recommended that the status of Write Enable and  $\overline{RDY}$  be checked, especially prior to an attempted modification of data. The 8 bits of the Status Register can be repeatedly output on SO after the initial Op-code. (See Figure 4 for timing).



### WRITE STATUS REGISTER (WRSR)

This instruction lets the user choose a Block Protection setting, and set or reset the WPEN bit. The values of the other data bits incorporated into WRSR can be 0 or 1, and are not stored in the Status Register. WRSR will be ignored unless both the following are true: a) WEN = 1, due to a prior WREN instruction; and b) Hardware Write Protection is not enabled. (See Table 4 for details). Except for the  $\overline{RDY}$  status, the values in the Status Register remain unchanged until the moment when the write cycle is complete and the register is updated. Note: WPEN can be changed from 1 to 0 only if  $\overline{WP}$  is already set High. Once completed, WEN is reset for complete chip write protection. (See Figure 5 for timing).

## READDATA (READ)

This instruction begins with the op-code and the 16-bit address, and causes the selected data byte to be shifted out on SO. Following this first data byte, additional sequential bytes are output. If the data byte in the highest address is output, the address rolls-over to the lowest address in the array, and the output could loop indefinitely. At any time, a rising  $\overline{\textbf{CS}}$  signal completes the operation. (See Figure 6 for timing).

## WRITE DATA (WRITE)

The WRITE instruction begins with the op-code, the 16-bit address of the first byte to be modified, and the first data byte. Additional data bytes may be written sequentially to the array after the first byte. Each WRITE instruction can affect the contents of a 64 byte page, but no more. The page begins at address XXXXXXXX XX000000, and ends with XXXXXXXXXXXX111111. If the last byte of the page is input, the address rolls over to the beginning of the same page. More than 64 data bytes can be input during the same instruction, but upon a completed write cycle, a page would only contain the last 64 bytes.

The region of the array defined within Block Protection cannot be modified as long as that block configuration is selected. The region of the array outside the Block Protection can only be modified if Write Enable (WEN) is set to 1. Therefore, it may be necessary that a WREN instruction occur prior to WRITE. Hardware Write Protection has no affect on the memory array. Once Write is completed, WEN is reset for complete chip write protection. (See Figure 7 for timing).

Table 5. Address Key

Name	IS25C128A	
A <sub>N</sub>	A <sub>13-</sub> A <sub>0</sub>	
Don't Care Bits	A <sub>15-</sub> A <sub>14</sub>	

**Table 4. Write Protection** 

WPEN	WP	Hardware Write Protection	WEN	Inside Block	Outside Block	Status Register (WPEN, BP1, BP0)
0	Х	Not Enabled	0	Read-only	Read-only	Read-only
0	Х	Not Enabled	1	Read-only	Unprotected	Unprotected
1	0	Enabled	0	Read-only	Read-only	Read-only
1	0	Enabled	1	Read-only	Unprotected	Read-only
X	1	Not Enabled	0	Read-only	Read-only	Read-only
X	1	Not Enabled	1	Read-only	Unprotected	Unprotected

**Note:** X = Don't care bit.



# **ABSOLUTE MAXIMUM RATINGS (1)**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	-0.5 to + 6.5	V
VP	Voltage on Any Pin	-0.5 to Vcc + 0.5	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Тѕтс	Storage Temperature	-65 to +150	°C
Іоит	Output Current	5	mA

#### Notes:

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

# **OPERATING RANGE (IS25C128A-2)**

Range	Ambient Temperature	Vcc
Industrial	–40°C to +85°C	1.8V to 5.5V

#### Note:

1. ISSI offers Industrial grade for Commercial applications (0°C to +70°C).

# **OPERATING RANGE (IS25C128A-3)**

Range	Ambient Temperature	Vcc
Automotive	-40°C to +125°C	2.5V to 5.5V

# CAPACITANCE(1,2)

Symbol	Parameter	Conditions	Max.	Unit
CIN	Input Capacitance	$V_{IN} = 0V$	6	pF
Соит	Output Capacitance	Vout = 0V	8	pF

#### Notes:

- Tested initially and after any design or process changes that may affect these parameters and not 100% tested.
- 2. Test conditions:  $T_A = 25^{\circ}C$ , f = 1 MHz,  $V_{CC} = 5.0V$ .



# DC ELECTRICAL CHARACTERISTICS

 $T_A = -40$ °C to +85°C for Industrial,  $T_A = -40$ °C to +125°C for Automotive.

Symbol	Parameter	<b>Test Conditions</b>	Min.	Max.	Unit
V <sub>OL1</sub>	Output LOW Voltage	Vcc = 5V, IoL = 3 mA	_	0.4	V
Vol2	Output LOW Voltage	Vcc = 2.5V, loL = 1.5 mA	_	0.4	V
Vol3	Output LOW Voltage	Vcc = 1.8V, IoL = 0.15 mA	_	0.2	V
V <sub>OH1</sub>	Output HIGH Voltage	Vcc = 5V, Iон = -3 mA	0.8 x Vcc	_	V
V <sub>OH2</sub>	Output HIGH Voltage	Vcc = 2.5V, loн = -0.4mA	0.8 x Vcc	_	V
Voн3	Output HIGH Voltage	Vcc = 1.8V, loн = -0.1mA	0.8 x Vcc	_	V
VIH	Input HIGH Voltage		0.7xVcc	Vcc + 1	V
VIL	Input LOW Voltage		-1.0	0.3 x Vcc	V
ILI	Input Leakage Current	VIN = 0V TO VCC	-3	3	μΑ
ILO	Output Leakage Current	Vout = 0V to Vcc, $\overline{\textbf{CS}}$ = Vcc	-3	3	μΑ

# **POWER SUPPLY CHARACTERISTICS**

 $T_A = -40^{\circ}C$  to  $+85^{\circ}C$  for Industrial.

Symbol	Parameter	<b>Test Conditions</b>	Min.	Max.	Unit
lcc1	Vcc Operating Current	Read/Write at 10 MHz (Vcc = 5V)	_	10.0	mA
Icc2	Vcc Operating Current	Read/Write at 5 MHz (Vcc = 2.5V)	_	4.0	mA
Icc3	Vcc Operating Current	Read/Write at 5 MHz (Vcc = 1.8V)	_	3.0	mA
ISB1	Standby Current	$Vcc = 5.0V$ , $Vin = Vcc$ or GND $\overline{CS} = Vcc$	_	25	μΑ
ISB2	Standby Current	Vcc = 2.5V, $Vin = Vcc$ or $GND\overline{CS} = Vcc$	_	20	μΑ
IsB3	Standby Current	$Vcc = 1.8V$ , $Vin = Vcc$ or $GND$ $\overline{CS} = Vcc$	_	15	μΑ

# **POWER SUPPLY CHARACTERISTICS**

 $T_A = -40^{\circ}C$  to  $+125^{\circ}C$  for Automotive.

Symbol	Parameter	<b>Test Conditions</b>	Min.	Max.	Unit
lcc1	Vcc Operating Current	Read/Write at 10 MHz (Vcc = 5V)	_	12.0	mA
lcc2	Vcc Operating Current	Read/Write at 5 MHz (Vcc = 2.5V)	_	5.0	mA
ISB1	Standby Current	$\frac{\text{Vcc} = 5.0\text{V}, \text{Vin} = \text{Vcc or GND}}{\overline{\text{CS}} = \text{Vcc}}$	_	30	μΑ
ISB2	Standby Current	$Vcc = 2.5V$ , $Vin = Vcc$ or $GND$ $\overline{CS} = Vcc$	_	20	μΑ



# **AC Characteristics**

 $T_A = -40^{\circ}C$  to  $+85^{\circ}C$  for Industrial.

		1.8V ≤ Vo	cc < 4.5V	4.5V ≤ Vo	cc ≤ 5.5V	
Symbol	Parameter	Min	Max	Min	Max	Units
fsck	SCK Clock Frequency	0	5	0	10	MHz
trı	Input Rise Time	_	2	_	2	μs
trı	Input Fall Time	_	2	_	2	μs
twн	SCK High Time	90	_	40	_	ns
twL	SCK Low Time	90	_	40	_	ns
tcs	CS High Time	100	_	40	_	ns
tcss	CS Setup Time	90	_	40	_	ns
tcsh	CS Hold Time	90	_	25	_	ns
tsu	Data In Setup Time	20	_	15	_	ns
tн	Data In Hold Time	30	_	15	_	ns
tho	Hold Setup Time	50	_	25	_	ns
tco	Hold Hold Time	50	_	25	_	ns
tv	Output Valid	0	60	0	25	ns
tно	Output Hold Time	0	_	0	_	ns
tız	Hold to Output Low Z	0	50	0	25	ns
tHZ	Hold to Output High Z	_	100	_	25	ns
tois	Output Disable Time	_	100	_	25	ns
twc	Write Cycle Time	_	5	_	5	ms

 $C_L = 100pF$ 



# **AC Characteristics**

 $T_A = -40^{\circ}C$  to  $+125^{\circ}C$  for Automotive.

		2.5V ≤ Vcc	2.5V ≤ Vcc < 4.5V			
Symbol	Parameter	Min	Max	Min	Max	Units
fsck	SCK Clock Frequency	0	5	0	10	MHz
trı	Input Rise Time	_	2	_	2	μs
tFI	Input Fall Time	_	2	_	2	μs
twн	SCK High Time	90	_	40	_	ns
twL	SCK Low Time	90	_	40	_	ns
tcs	CS High Time	100	_	40	_	ns
tcss	CS Setup Time	90	_	40	_	ns
tcsH	CS Hold Time	90	_	25	_	ns
tsu	Data In Setup Time	20	_	15	_	ns
tн	Data In Hold Time	30	_	15	_	ns
tho	Hold Setup Time	50	_	25	_	ns
tcd	Hold Time	50	_	25	_	ns
tv	Output Valid	0	60	0	25	ns
tho	Output Hold Time	0	_	0	_	ns
tız	Hold to Output Low Z	0	50	0	25	ns
tHZ	Hold to Output High Z	_	100	_	25	ns
tois	Output Disable Time	_	100	_	25	ns
twc	Write Cycle Time	_	5	_	5	ms

 $C_L = 100pF$ 



# **TIMING DIAGRAMS**

Figure 1. Synchronous Data Timing

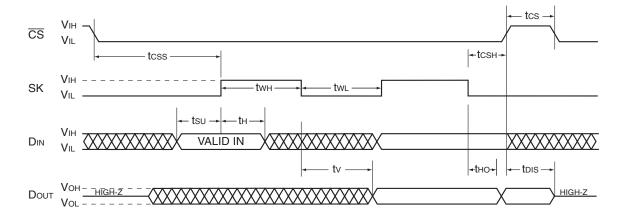


Figure 2. WREN Timing

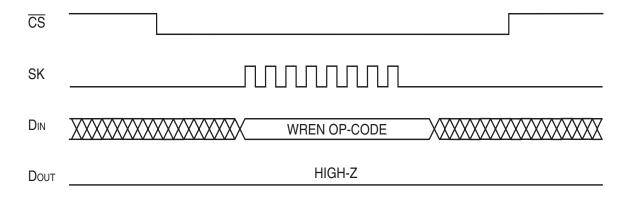


Figure 3. WRDI Timing

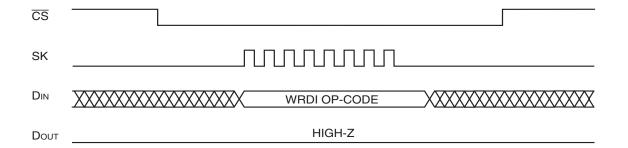
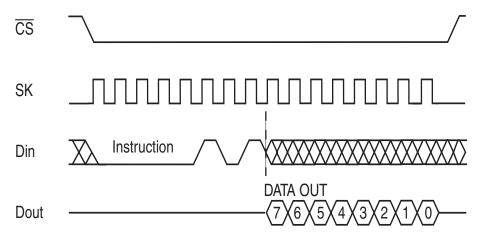


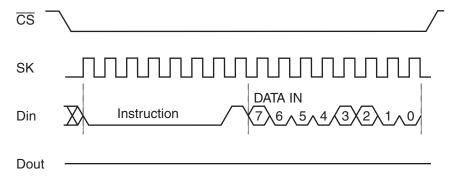


Figure 4. RDSR Timing



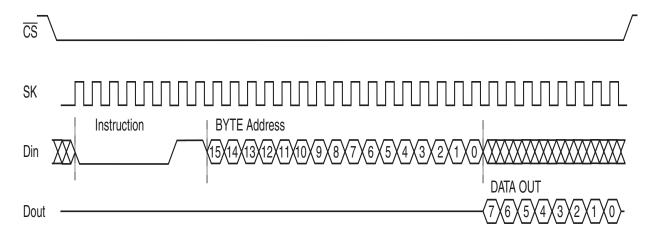
Note: The "Don't Care" bit of the op-code is set to 0 in the above instruction for consistency.

Figure 5. WRSR Timing



Note: The "Don't Care" bit of the op-code is set to 0 in the above instruction for consistency.

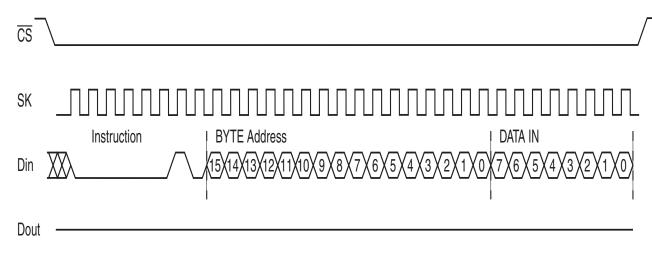
Figure 6. READ Timing



Note: The "Don't Care" bit of the op-code is set to 0 in the above instruction for consistency.



Figure 7. WRITE Timing



Note: The "Don't Care" bit of the op-code is set to 0 in the above instruction for consistency.

# Figure 8. **HOLD** Timing

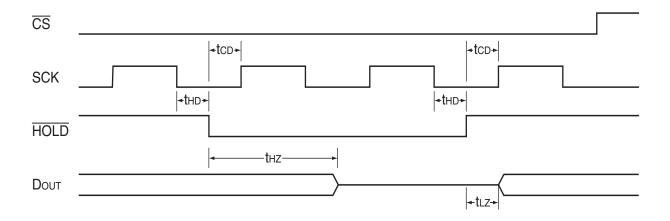




Figure 9. Entry into Deep Sleep Timing

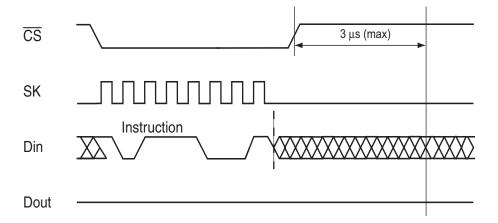
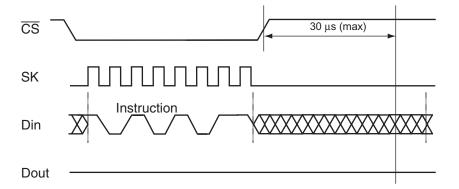


Figure 10. Release from Deep Sleep Timing





# **ORDERING INFORMATION**

Industrial Range: -40°C to +85°C

Voltage		
Range	Part Number	Package
1.8V	IS25C128A-2GI	Small Outline (JEDEC STD)
to 5.5V	IS25C128A-2GLI	Small Outline (JEDEC STD), Lead-free
	IS25C128A-2PI	300-mil Plastic DIP
	IS25C128A-2PLI	300-mil Plastic DIP, Lead-free
	IS25C128A-2ZI	8-pin TSSOP
	IS25C128A-2ZLI	8-pin TSSOP, Lead-free
	IS25C128A-2WI	Small Outline (EIAJ STD)
	IS25C128A-2WLI	Small Outline (EIAJ STD), Lead-free

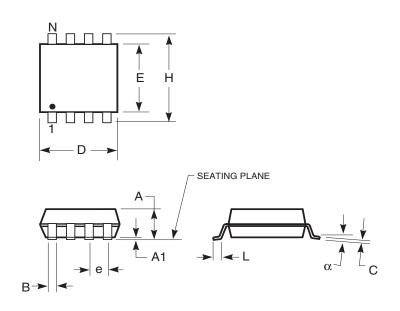
# **ORDERING INFORMATION**

Automotive Range: -40°C to +125°C

Voltage	Doublesshor	Dealine
Range	Part Number	Package
2.5V	IS25C128A-3GLA3	Small Outline (JEDEC STD), Lead-free
to 5.5V	IS25C128A-3PLA3	300-mil Plastic DIP, Lead-free
	IS25C128A-3ZAL3	8-pin TSSOP, Lead-free
	IS25C128A-3WLA3	Small Outline (EIAJ STD), Lead-free



200-mil Plastic SOP Package Code: W



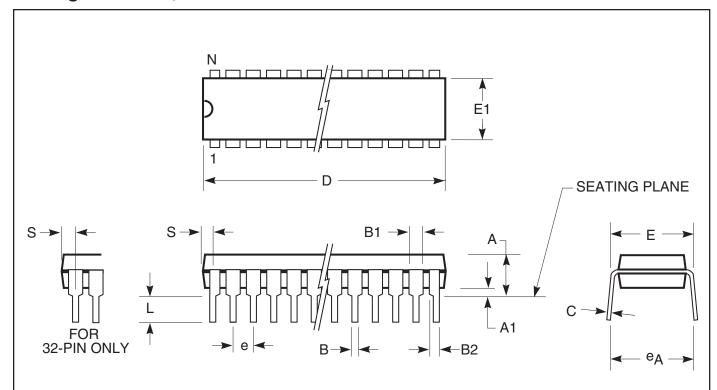
#### Notes:

- 1. Controlling dimension: mm, unless otherwise specified.
- BSC = Basic lead spacing between centers.
   Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.

	2	00-mil Plas	tic SOP (W)		
Symbol	Min	Max	Min	Max	
Ref. Std.	Ind	ches	mm		
No. Leads		8	8		
Α	_	0.085	_	2.16	
A1	0.004	0.009	0.10	0.23	
В	0.014	0.018	0.35	0.45	
С	0.006	0.014	0.15	0.35	
D	0.203	0.211	5.15	5.35	
Е	0.204	0.213	5.18	5.40	
Н	0.303	0.325	7.70	8.26	
е	0.05	0 BSC	1.27 B	SC	
L	0.020	0.033	0.51	0.85	



300-mil Plastic DIP Package Code: N,P



	MILLIMETERS		INCHES		
Sym.	Min.	Max.	Min.	Max.	
N0. Leads		8			
Α	3.68	4.57	0.145	0.180	
A1	0.38	_	0.015	_	
В	0.36	0.56	0.014	0.022	
B1	1.14	1.52	0.045	0.060	
B2	0.81	1.17	0.032	0.046	
С	0.20	0.33	0.008	0.013	
D	9.12	9.53	0.359	0.375	
E	7.62	8.26	0.300	0.325	
E1	6.20	6.60	0.244	0.260	
ед	8.13	9.65	0.320	0.380	
е	2.54 BSC		0.100 BSC		
L	3.18	_	0.125		
S	0.64	0.762	0.025	0.030	

#### Notes:

- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

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300-mil Plastic DIP Package Code: N,P

	MILLIMETERS		INCHES		
Sym.	Min.	Max.	Min.	Max.	
N0. Leads	1	6			
Α	3.68	4.57	0.145	0.180	
A1	0.25	_	0.010	_	
В	0.46 BSC		0.018	BSC	
B1	1.52	BSC	0.060 BSC		
B2	_	_	_	_	
С	0.13	0.38	0.005	0.015	
D	18.92	19.18	0.745	0.755	
E	7.44	8.13	0.293	0.320	
E1	6.22	6.48	0.245	0.255	
e <sub>A</sub>	8.13	9.65	0.320	0.380	
e	2.54 BSC		0.100 BSC		
L	3.05	3.56	0.120	0.140	
S	0.38	0.89	0.015	0.035	

	MILL	IMETERS	INCHES		
Sym.	Min.	Max.	Min.	Max.	
N0. Leads		20			
A	3.68	4.57	0.145	0.180	
A1	0.38	_	0.015	_	
В	0.36	0.56	0.014	0.022	
B1	1.14	1.78	0.045	0.070	
B2	_	_	_	_	
С	0.20	0.36	0.008	0.014	
D	25.91	26.42	1.020	1.040	
E	7.49	8.26	0.295	0.325	
E1	6.01	7.11	0.240	0.280	
e <sub>A</sub>	_	10.92	_	0.430	
e	2.	54 BSC	0.100	BSC	
L	3.05	3.81	0.120	0.150	
S	1.02	1.52	0.040	0.060	

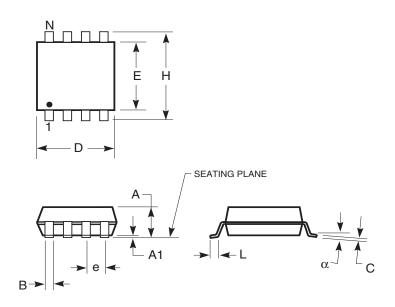
	MILLIMETERS		INCHES		
Sym.	Min.	Max.	Min.	Max.	
N0. Leads		28			
A	3.68	4.57	0.145	0.180	
A1	0.25	_	0.010	_	
В	0.41	0.56	0.016	0.022	
B1	1.27	1.78	0.050	0.070	
B2	0.81	1.17	0.032	0.046	
С	0.20	0.38	0.008	0.015	
D	35.05	35.56	1.380	1.400	
E	7.49	8.00	0.295	0.315	
E1	6.99	7.49	0.275	0.295	
e <sub>A</sub>	7.87	10.16	0.310	0.400	
е	2.54 BSC		0.100	) BSC	
L	3.05	3.81	0.120	0.150	
S	0.51	1.06	0.020	0.042	

	MILLIMETERS		INC	HES
Sym.	Min.	Max.	Min.	Max.
N0. Leads		32		
Α	3.56	4.57	0.140	0.180
A1	0.38	_	0.015	_
В	0.38	0.53	0.015	0.021
B1	1.02	1.78	0.040	0.070
B2	_	_	_	_
С	0.13	0.38	0.005	0.015
D	40.51	40.77	1.595	1.605
E	7.75	8.26	0.305	0.325
E1	7.24	7.22	0.285	0.292
ед	8.38	9.40	0.33	0.370
е	2.54 BSC		0.100	) BSC
L	3.05	3.81	0.120	0.150
S	1.65	2.16	0.065	0.085





150-mil Plastic SOP Package Code: G, GR



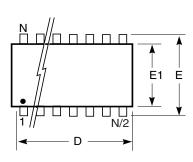
150-mil Plastic SOP (G, GR)					
Symbol	Min	Max	Min	Max	
Ref. Std.	Inc	hes	mm		
No. Leads		8	8		
Α	_	0.068	_	1.73	
A1	0.004	0.009	0.1	0.23	
В	0.013	0.020	0.33	0.51	
С	0.007	0.010	0.18	0.25	
D	0.189	0.197	4.8	5	
Е	0.150	0.157	3.81	3.99	
Н	0.228	0.245	5.79	6.22	
е	e 0.050 BSC 1.27 BSC		SC SC		
L	0.020	0.035	0.51	0.89	

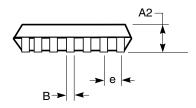
#### Notes

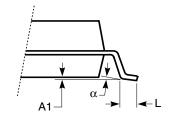
- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- 4. Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

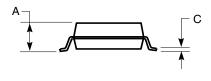


Thin Shrink Small Outline TSSOP Package Code: Z (8 pin, 14 pin)









TSSOP (Z)									
Ref. Std.	Ref. Std. JEDEC MO-153								
No. Leads	o. Leads 8								
	Millimeters		Inches						
Symbol	Min	Max	Min	Max					
A	_	1.20	_	0.047					
A1	0.05	0.15	0.002	0.006					
A2	0.80	1.05	0.032	0.041					
В	0.19	0.30	0.007	0.012					
С	0.09	0.20	0.004	0.008					
D	2.90	3.10	0.114	0.122					
E1	4.30	4.50	0.169	0.177					
Е	6.40 BSC		0.252 BSC						
е	0.65 BSC		0.026 BSC						
L	0.45	0.75	0.018	0.030					
α	_	8°	_	8°					

TSSOP (Z)									
Ref. Std. JEDEC MO-153									
No. Leads 14									
	Millim	eters	Inch	es					
Symbol	Min	Max	Min	Max	_				
A	_	1.20	_	0.047	_				
A1	0.05	0.15	0.002	0.006					
A2	0.80	1.05	0.031	0.041					
В	0.19	0.30	0.007	0.012					
С	0.09	0.20	0.0035	0.008					
D	4.90	5.10	0.193	0.201					
E1	4.30	4.50	0.170	0.177					
Е	6.40 BSC		0.25	0.252 BSC					
е	0.65 BSC		0.026 BSC						
L	0.45	0.75	0.0177	0.0295					
α	_	8°	_	8°					

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